



THE DATASHEET OF BS170P



N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 - SEPT 93

FEATURES

- * 60 Volt V_{DS}
- * $R_{DS(on)} = 5\Omega$

REFER TO ZVN3306A FOR GRAPHS

ABSOLUTE MAXIMUM RATINGS

PARAMETER
Drain-Source Voltage
Continuous Drain Current at $T_{amb} = 25^\circ$
Pulsed Drain Current
Gate-Source Voltage
Power Dissipation at $T_{amb} = 25^\circ\text{C}$
Operating and Storage Temperature Range

ELECTRICAL CHARACTERISTICS



PARAMETER	SYMBOL	MIN
Drain-Source Breakdown Voltage	BV_{DSS}	60
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.8
Gate Body Leakage	I_{GSS}	
Zero Gate Voltage Drain Current	I_{DSS}	
Static Drain-Source on-State Resistance (1)	$R_{DS(on)}$	
Forward Transconductance (1)(2)	g_{fs}	
Input Capacitance (2)	C_{iss}	
Turn-On Time (2)(3)	$t_{(on)}$	
Turn-Off Time (2)(3)	$t_{(off)}$	

(1) Measured under pulsed conditions. Pul

(3) Switching times measured with a 50 Ω s

Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

-  [View BS170P on WIN SOURCE](#)
-  [Diodes Incorporated Information](#)

Optimize Your Supply Chain with WIN SOURCE Solutions

-  Global Sourcing Solution
-  Obsolete Management
-  Cost Control Management
-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management